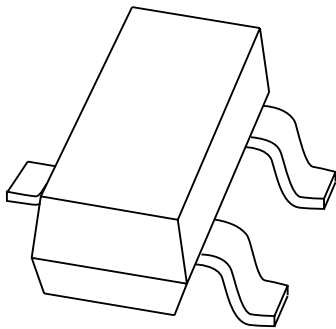


DATA SHEET



PBSS4230T

30 V, 2 A

NPN low V_{CEsat} (BISS) transistor

Product specification

2003 Sep 29

**30 V, 2 A
NPN low V_{CEsat} (BISS) transistor**

PBSS4230T

FEATURES

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High efficiency leading to less heat generation
- Reduced printed-circuit board requirements
- Cost effective alternative to MOSFETs in specific applications.

APPLICATIONS

- Power management
 - DC/DC conversion
 - Supply line switching
 - Battery charger
 - LCD backlighting.
- Peripheral driver
 - Driver in low supply voltage applications (e.g. lamps and LEDs)
 - Inductive load drivers (e.g. relays, buzzers and motors).

DESCRIPTION

NPN BISS transistor in a SOT23 plastic package providing ultra low V_{CEsat} and R_{CEsat} parameters.
PNP complement: PBSS5230T.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
PBSS4230T	*3D

Note

1. * = p: made in Hong Kong.
* = t: made in Malaysia.
* = W: made in China.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PBSS4230T	–	plastic surface mounted package; 3 leads	SOT23

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	30	V
I_C	collector current (DC)	2	A
I_{CM}	peak collector current	3	A
R_{CEsat}	equivalent on-resistance	200	m Ω

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

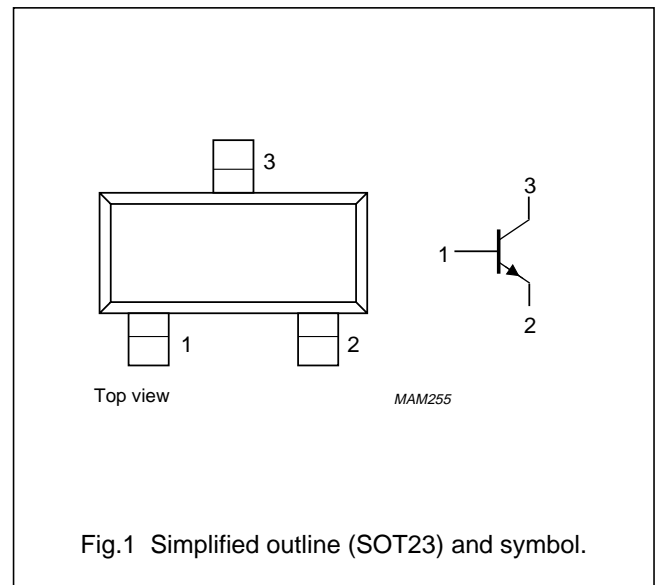


Fig.1 Simplified outline (SOT23) and symbol.

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	40	V
V_{CEO}	collector-emitter voltage	open base	–	30	V
V_{EBO}	emitter-base voltage	open collector	–	5	V
I_C	collector current (DC)		–	2	A
I_{CM}	peak collector current		–	3	A
I_{BM}	peak base current		–	300	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	300	mW
		$T_{amb} \leq 25\text{ °C}$; note 2	–	480	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Notes

1. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, standard footprint.
2. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm².

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air; note 1	417	K/W
		in free air; note 2	260	K/W

Notes

1. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, standard footprint.
2. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm².

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CHARACTERISTICS $T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{CB} = 30\text{ V}; I_E = 0$	–	–	100	nA
		$V_{CB} = 30\text{ V}; I_E = 0; T_J = 150\text{ °C}$	–	–	50	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 4\text{ V}; I_C = 0$	–	–	100	nA
h_{FE}	DC current gain	$V_{CE} = 2\text{ V}; I_C = 100\text{ mA}$	350	470	–	
		$V_{CE} = 2\text{ V}; I_C = 500\text{ mA}$	300	450	–	
		$V_{CE} = 2\text{ V}; I_C = 1\text{ A}$	300	420	–	
		$V_{CE} = 2\text{ V}; I_C = 2\text{ A}$	150	250	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 100\text{ mA}; I_B = 1\text{ mA}$	–	45	70	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	–	70	100	mV
		$I_C = 750\text{ mA}; I_B = 15\text{ mA}$	–	120	180	mV
		$I_C = 1\text{ A}; I_B = 50\text{ mA}; \text{note 1}$	–	130	180	mV
		$I_C = 2\text{ A}; I_B = 200\text{ mA}; \text{note 1}$	–	240	320	mV
R_{CEsat}	equivalent on-resistance	$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	140	200	$\text{m}\Omega$
V_{BEsat}	base-emitter saturation voltage	$I_C = 2\text{ A}; I_B = 200\text{ mA}; \text{note 1}$	–	–	1.1	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = 2\text{ V}; I_C = 100\text{ mA}$	–	–	0.75	V
f_T	transition frequency	$I_C = 100\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	100	230	–	MHz
C_c	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_e = 0; f = 1\text{ MHz}$	–	15	20	pF

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

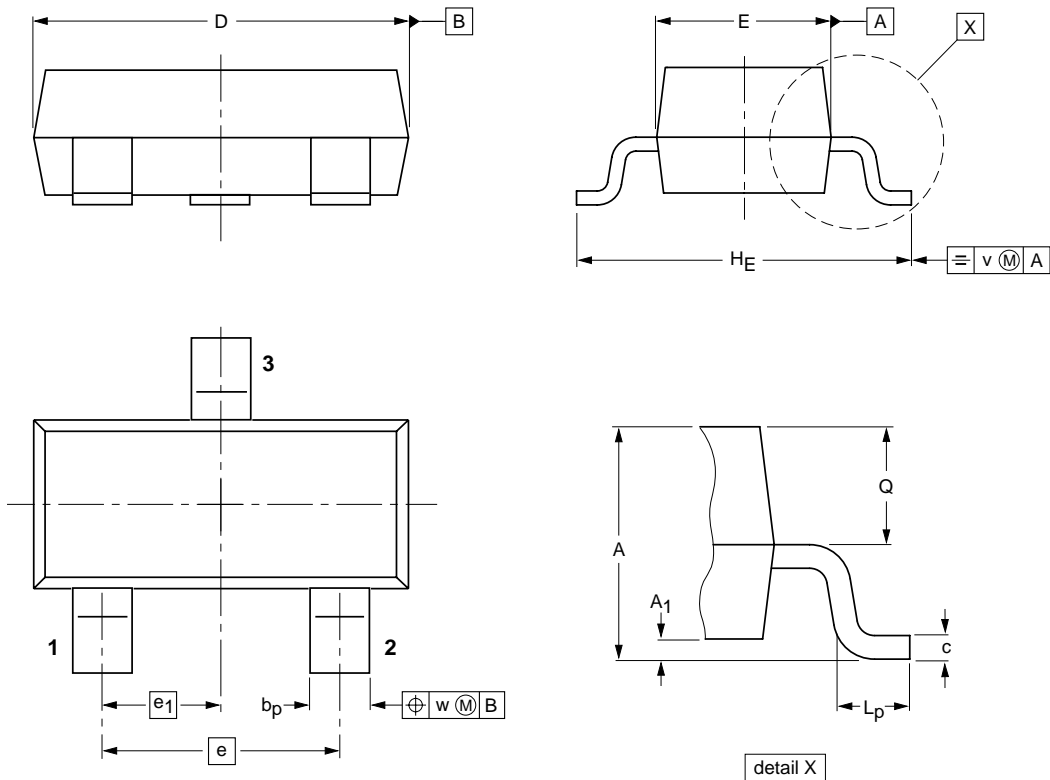
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PBSS4230T

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				97-02-28- 99-09-13

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PBSS4230T

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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Printed in The Netherlands

R75/01/pp7

Date of release: 2003 Sep 29

Document order number: 9397 750 11898

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